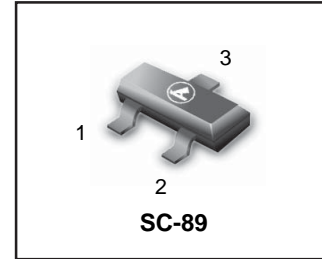


# Common Cathode Silicon Dual Switching Diode

This Common Cathode Silicon Epitaxial Planar Dual Diode is designed for use in ultra high speed switching applications. This device is housed in the SC-89 package which is designed for low power surface mount applications, where board space is at a premium.

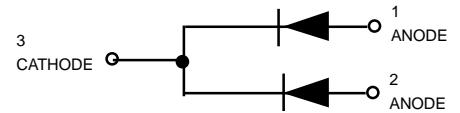
- Fast  $t_{rr}$
- Low  $C_D$
- Available in 8 mm Tape and Reel

## LDAN222T1



### MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

Rating	Symbol	Value	Unit
Reverse Voltage	$V_R$	80	Vdc
Peak Reverse Voltage	$V_{RM}$	80	Vdc
Forward Current	$I_F$	100	mAdc
Peak Forward Current	$I_{FM}$	300	mAdc
Peak Forward Surge Current	$I_{FSM}(1)$	2.0	Adc



### THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Power Dissipation	$P_D$	150	mW
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to +150	$^\circ\text{C}$

1.  $t = 1 \mu\text{s}$

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ )

Characteristic	Symbol	Condition	Min	Max	Unit
Reverse Voltage Leakage Current	$I_R$	$V_R = 70 \text{ V}$	—	0.1	$\mu\text{Adc}$
Forward Voltage	$V_F$	$I_F = 100 \text{ mA}$	—	1.2	Vdc
Reverse Breakdown Voltage	$V_R$	$I_R = 100 \mu\text{A}$	80	—	Vdc
Diode Capacitance	$C_D$	$V_R = 6.0 \text{ V}, f = 1.0 \text{ MHz}$	—	3.5	pF
Reverse Recovery Time	$t_{rr}(2)$	$I_F = 5.0 \text{ mA}, V_R = 6.0 \text{ V}, R_L = 100 \Omega, I_{rr} = 0.1 I_R$	—	4.0	ns

2.  $t_{rr}$  Test Circuit on following page.

### Driver Marking

LDAN222T1=N9

LDAN222T1

Electrical characteristic curves

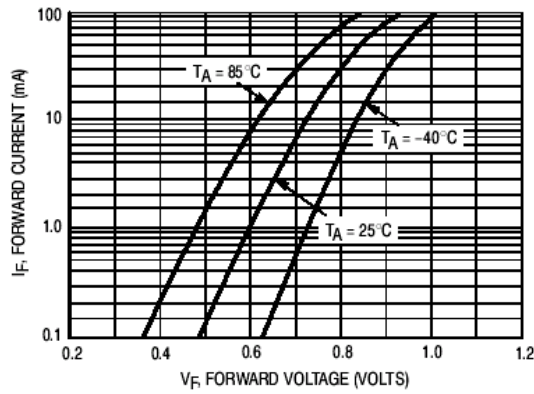


Figure 1. Forward Voltage

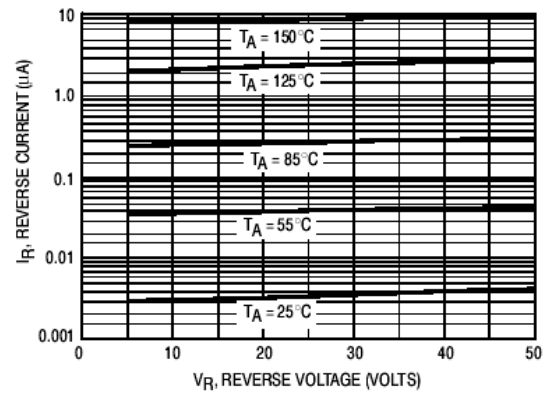


Figure 2. Reverse Current

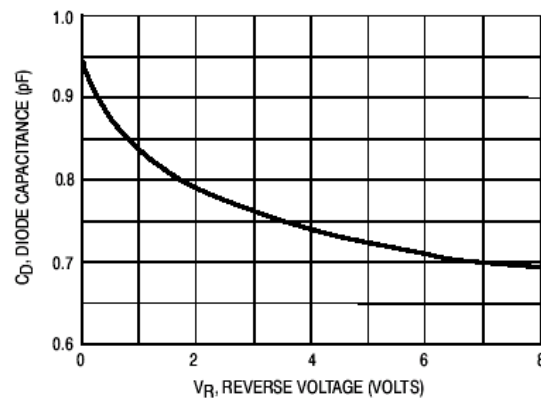
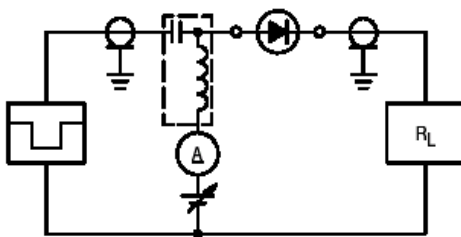
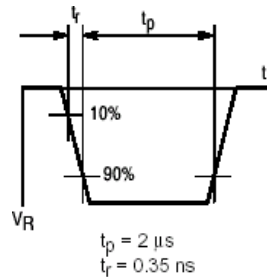


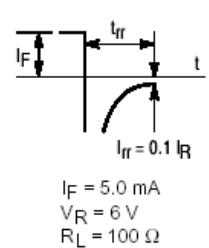
Figure 3. Diode Capacitance



RECOVERY TIME EQUIVALENT TEST CIRCUIT



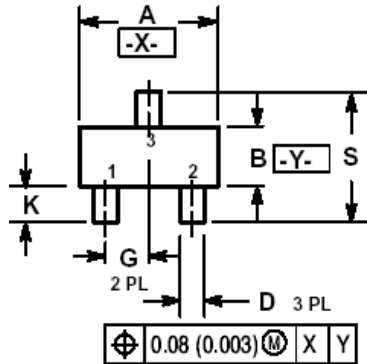
INPUT PULSE



OUTPUT PULSE

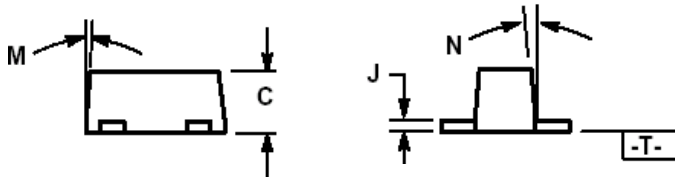
LDAN222T1

SC-89



NOTES:

- 1.DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2.CONTROLLING DIMENSION: MILLIMETERS
- 3.MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4.463C-01 OBSOLETE, NEW STANDARD 463C-02.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.60	1.70	0.059	0.063	0.067
B	0.75	0.85	0.95	0.030	0.034	0.040
C	0.60	0.70	0.80	0.024	0.028	0.031
D	0.23	0.28	0.33	0.009	0.011	0.013
G	0.50 BSC			0.020 BSC		
H	0.53 REF			0.021 REF		
J	0.10	0.15	0.20	0.004	0.006	0.008
K	0.30	0.40	0.50	0.012	0.016	0.020
L	1.10 REF			0.043 REF		
M	---	---	10 °	---	---	10 °
N	---	---	10 °	---	---	10 °
S	1.50	1.60	1.70	0.059	0.063	0.067

